

Charles University Prague  
Institute of Particle and Nuclear Physics

# Laser Tests of Silicon Detectors

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## Progress of laser tests in Prague

1. Testing algorithms of strip detectors tuned
2. Set of standard tests and analysis: focusing, strip response, charge sharing
3. Different wavelengths: 650nm and 1060nm used
4. Angle (tilt) scans
5. Optical header for direct beam power measurements in progress
6. Simulations of laser beam in Si (Zbyněk Drásal talk)
7. Deeper understanding of laser beam interaction with Si detectors
8. DST data format for test beams prepared (are they good for laser tests?)
9. Preparing of analysis macros based on DST starting
10. Future plans/fields of interest



## Testing algorithms of strip detectors

Complex test system integrates

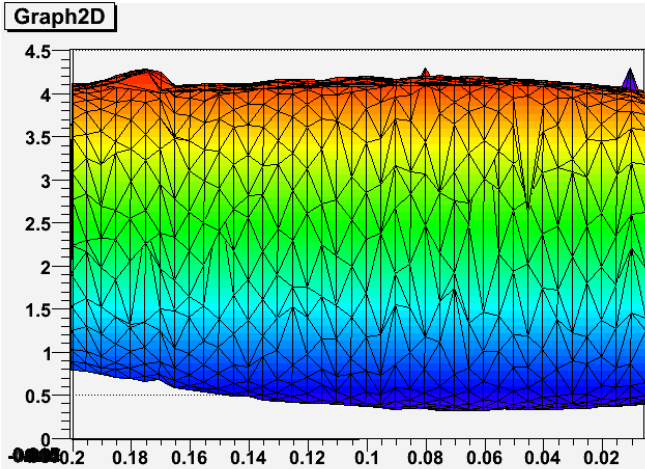
- DAQ sw (VME – NI PCI-VME )
- oscilloscope (GPIB)
- pulse generator (GPIB)
- position stages 3D-2R (USB)
- 2x power supplies (USB-RS232)

ROOT based software allows

- High voltage (bias) checking
- Focusing algorithms – rough, fine
- Position scans
- Timing scans
- Tilted scans
- Tilted scans with deep focusing
- Environmental parameters monitoring (temperature, humidity, power drops, bias drops, remote access and full processing from any place (VNC), automatic emergency system

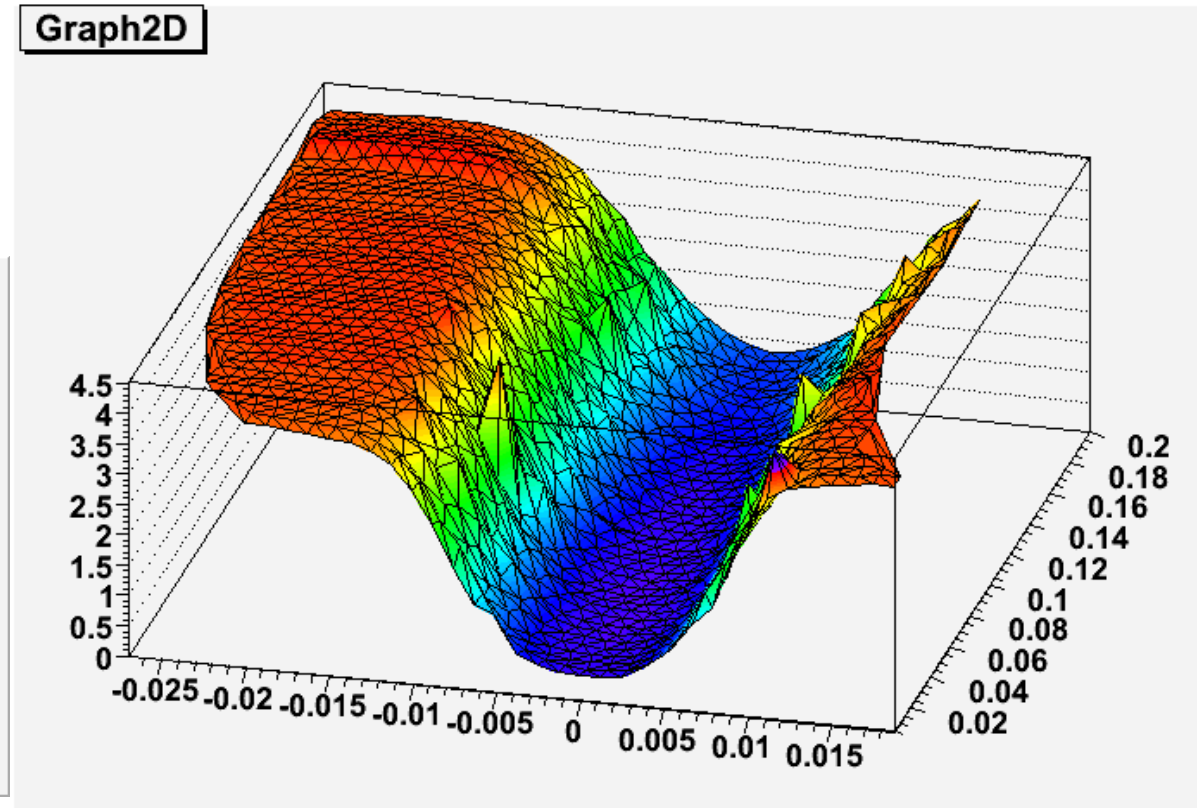
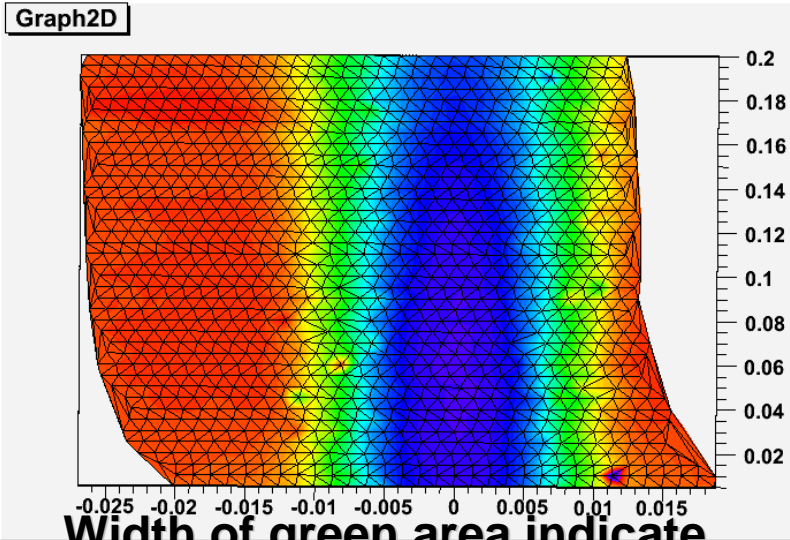


# Set of standard tests and analysis: focusing, strip response, charge sharing



Detail of looking of minima  
(flat in  $60\mu\text{m}$  range)

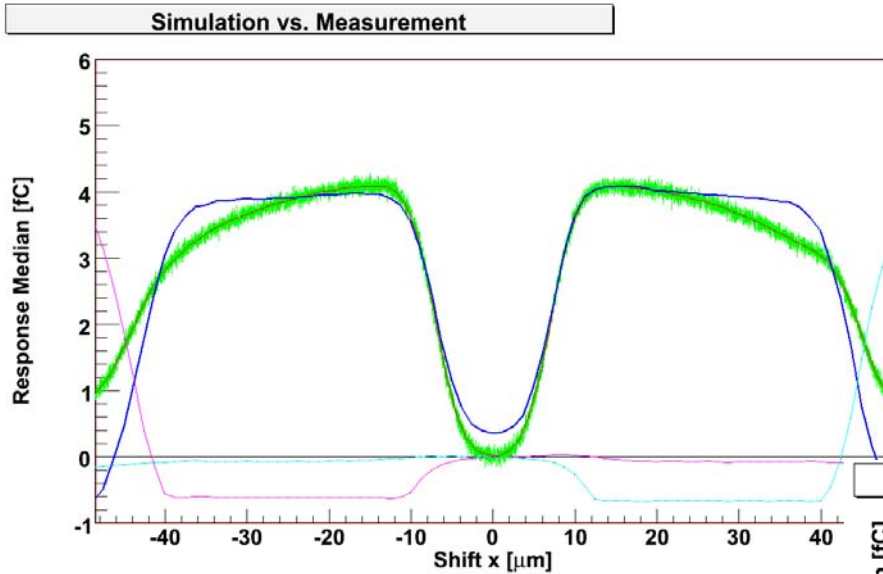
Example of focusing  
matrix



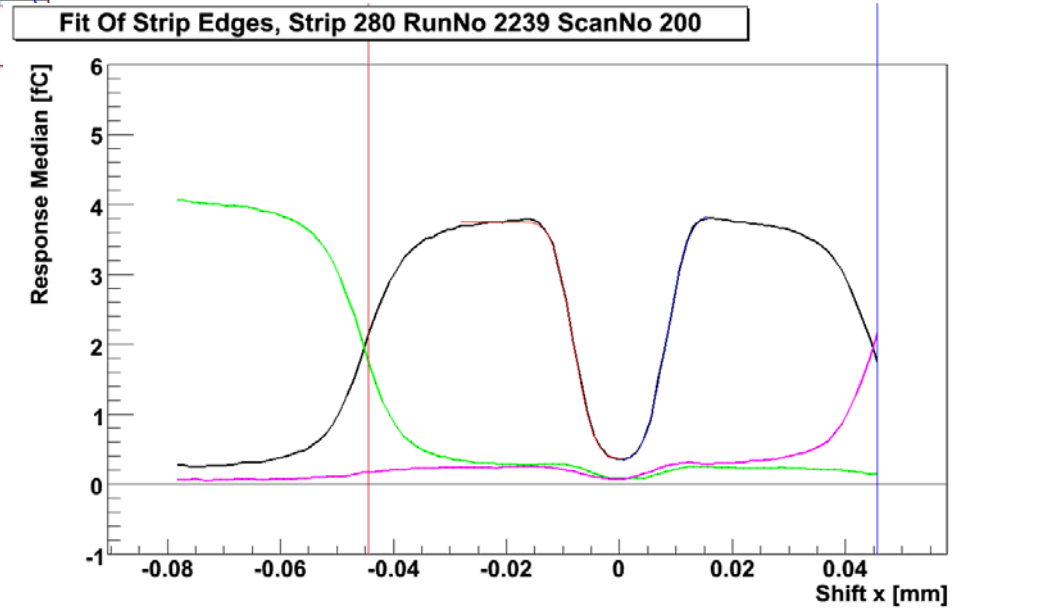
Width of green area indicate  
focusing width of laser beam



## Different wavelengths: 650nm and 1060nm



CiS detector: 650 wavelength,  
differences from simulations, negative  
charge induced in neighbored



CiS detector: 1060 wavelength – in  
very good agreement with simulations

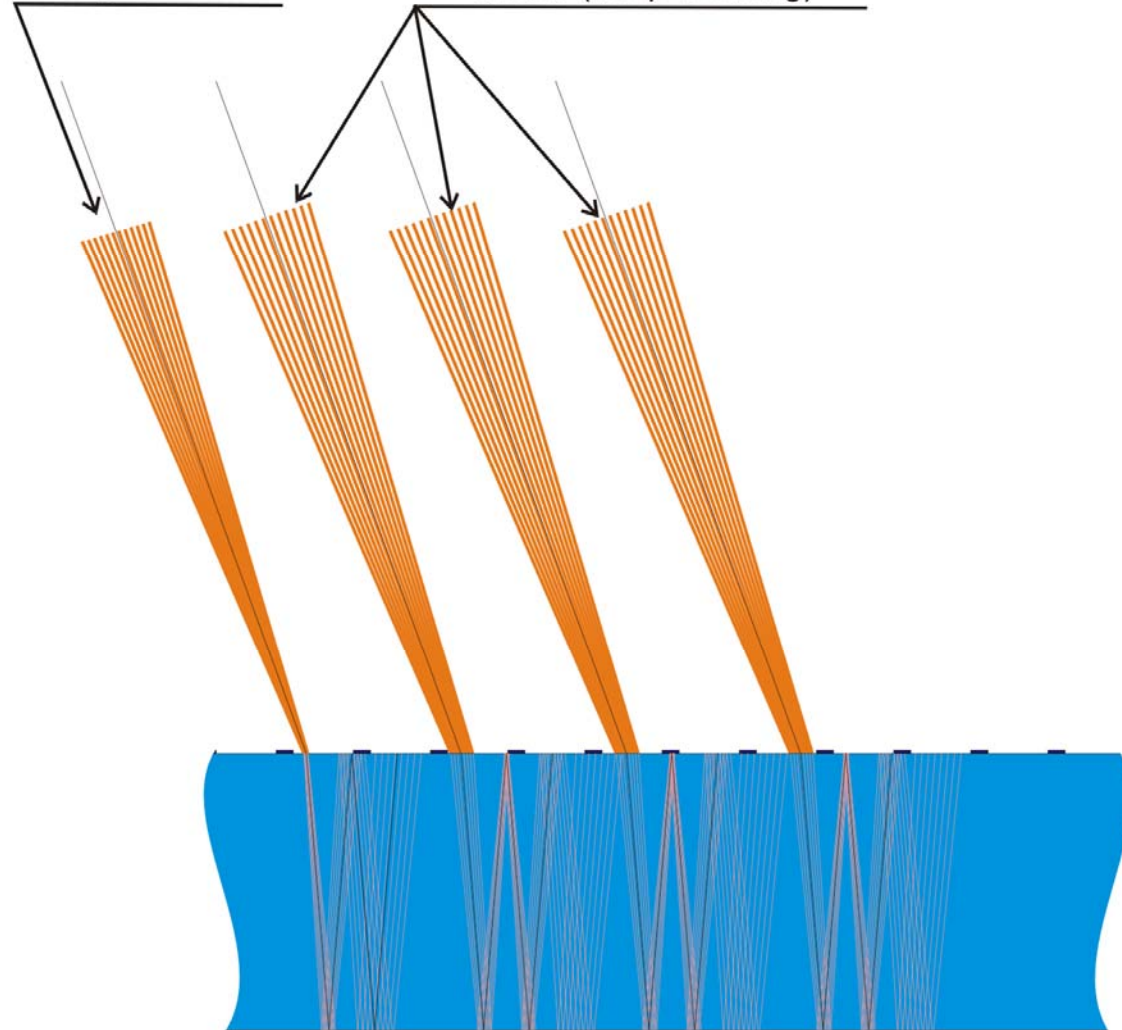


# Angle (tilt) scans (1)

Tilt laser beam

Standard focusing  
to top surface

Focusing to top surface from  
inside (deep focusing)

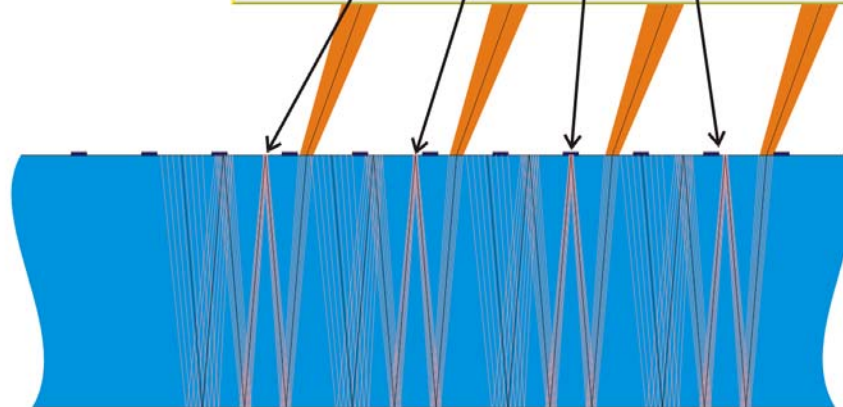
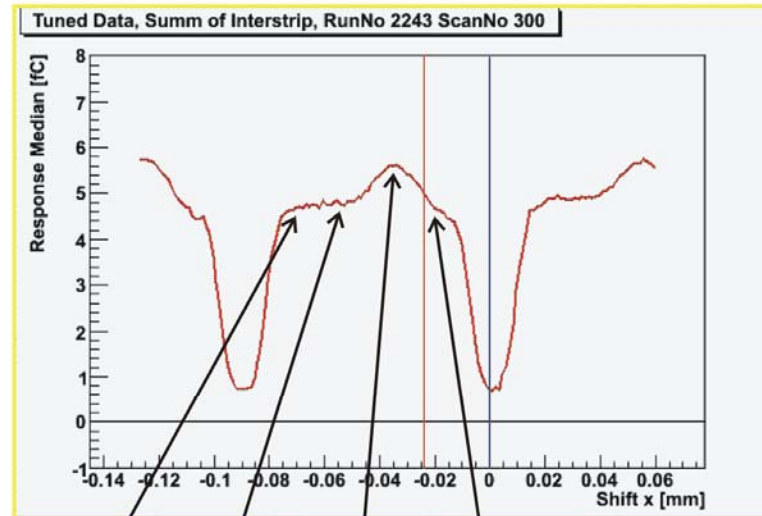




## Angle (tilt) scans (2)

Tilt laser beam

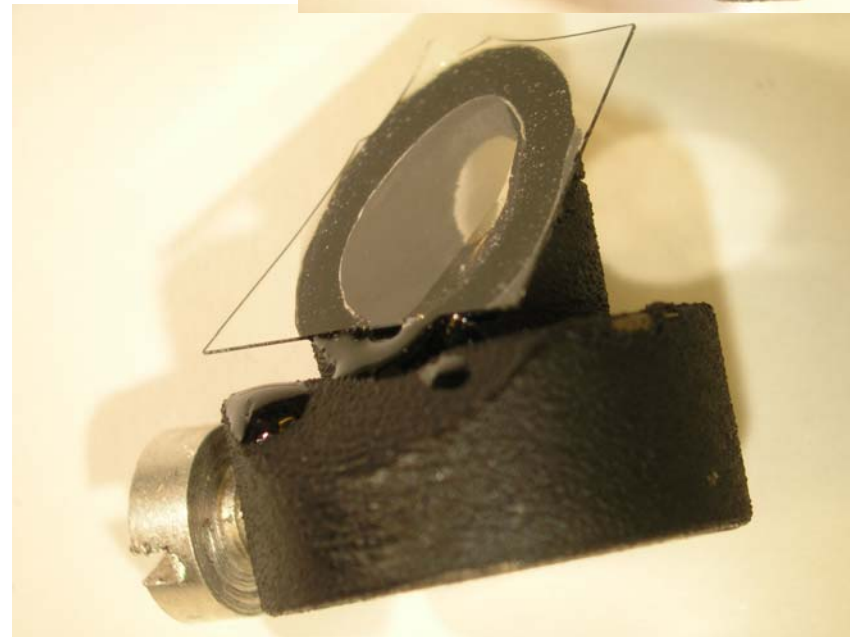
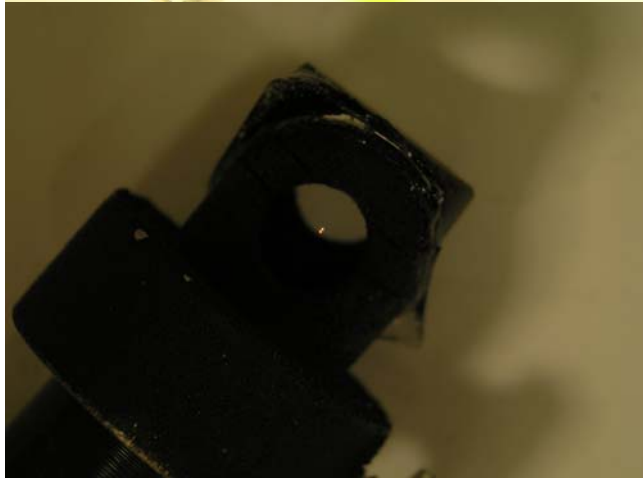
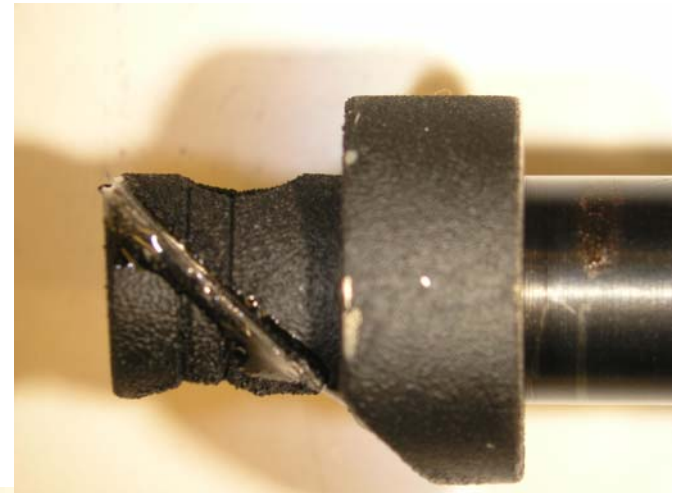
Focusing to top surface from  
inside (deep focusing)





# Optical head for power monitoring and reflectance measurement

1. Mechanical design and manufacturing done
2. Readout electronics under construction

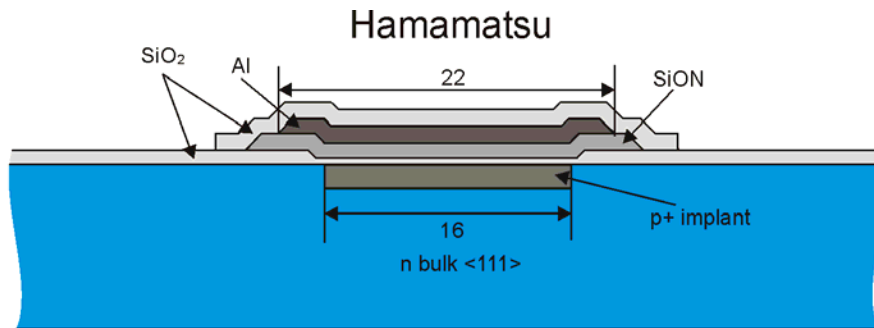




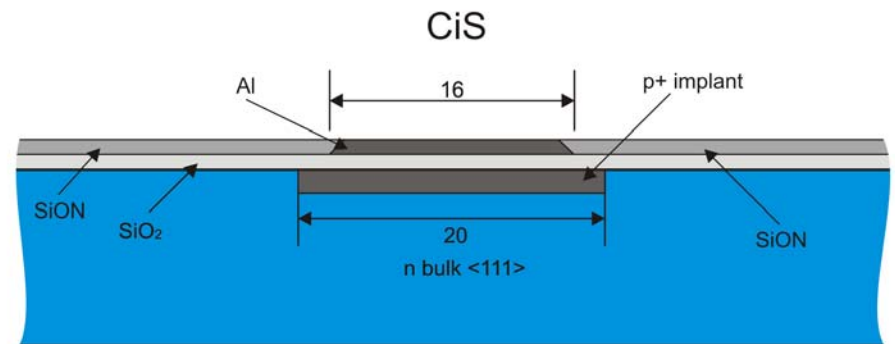
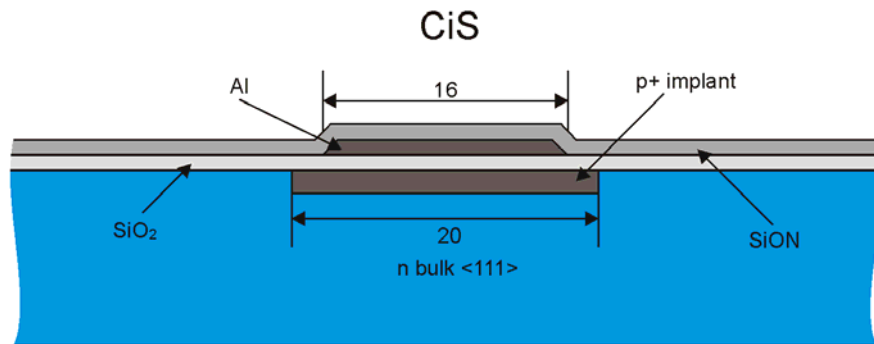
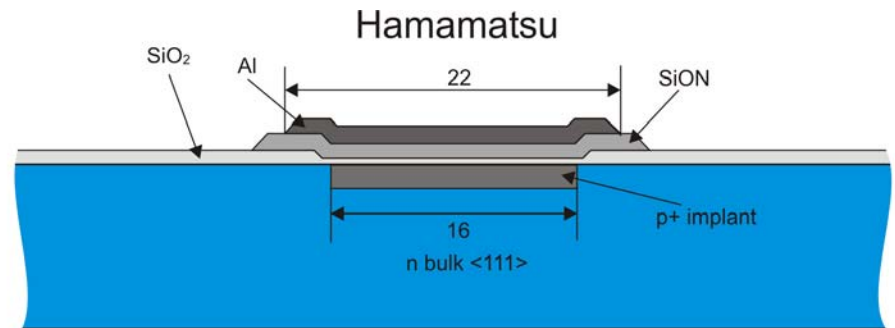


# Deeper understanding of laser beam interaction with Si detectors

Surface structure on strip



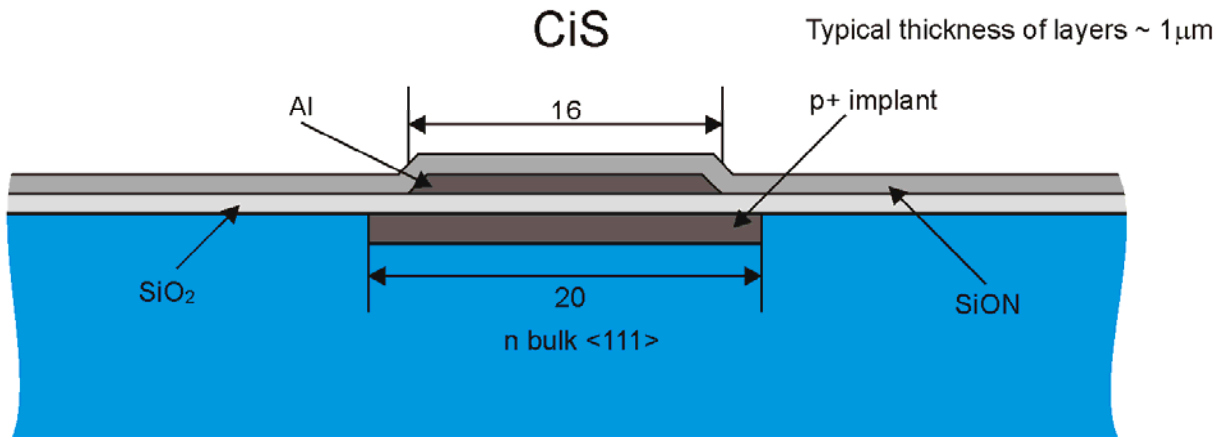
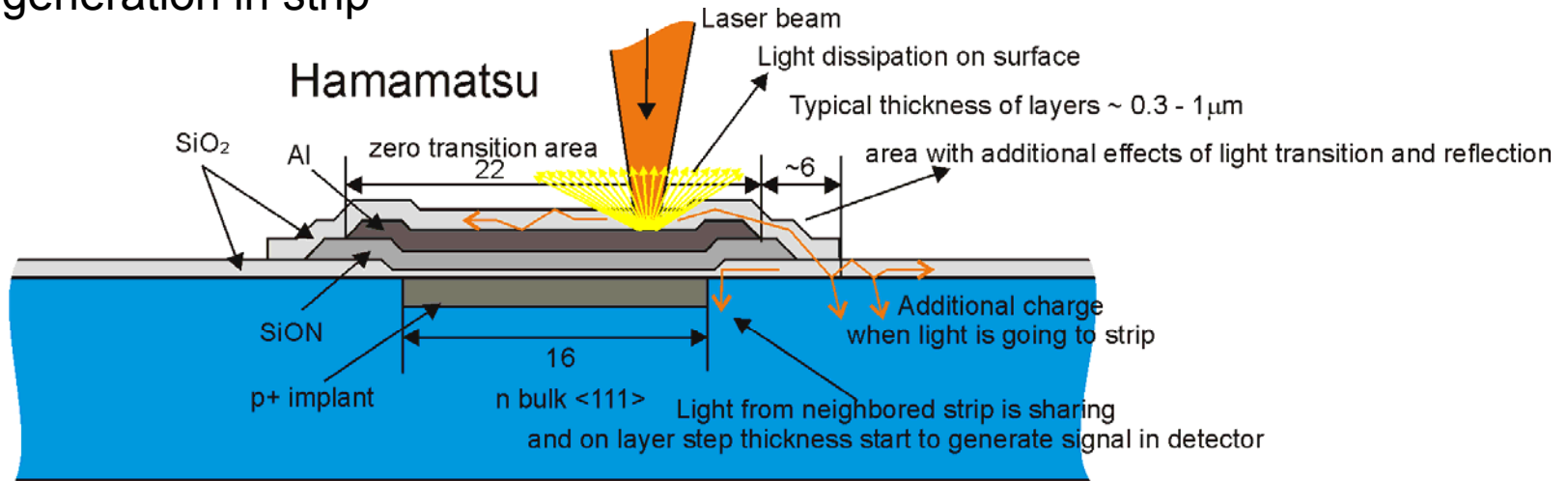
Surface structure on bond pad





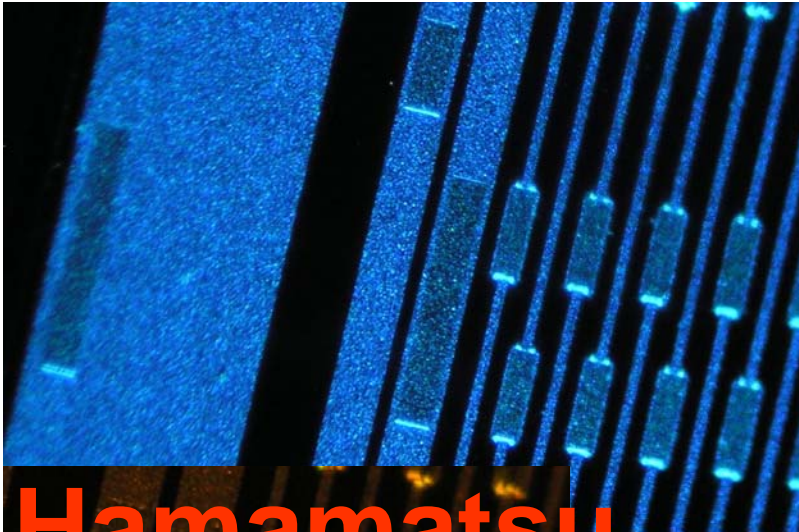
# Deeper understanding of laser beam interaction with Si detectors

## Charge generation in strip

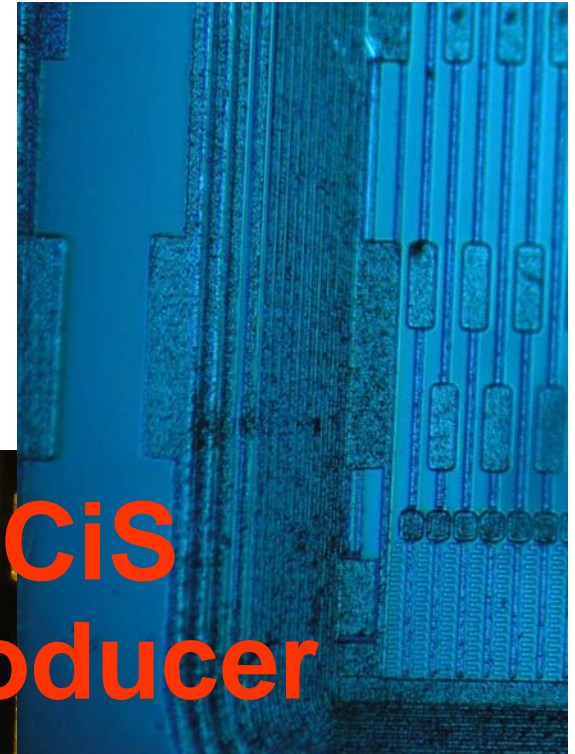




## Deeper understanding of laser beam interaction with Si detectors

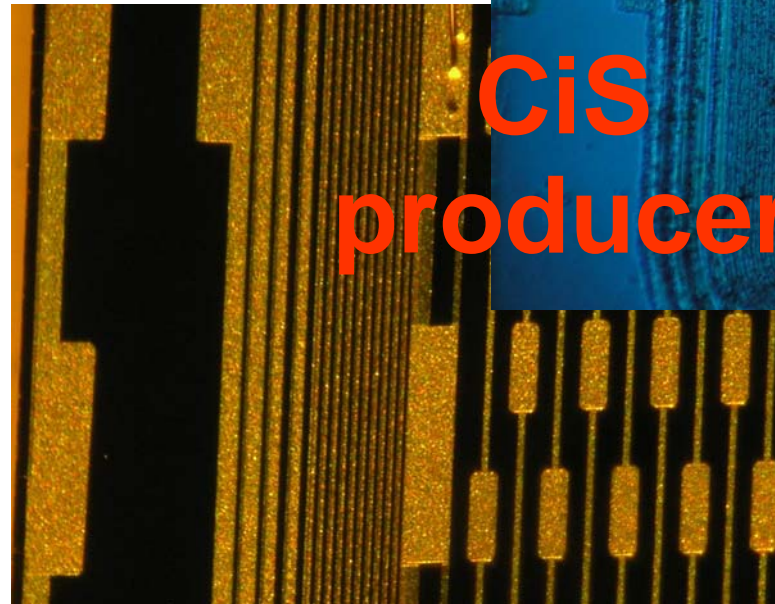


1. Surface
2. Coating
3. Thickness
4. Size
5. Technology



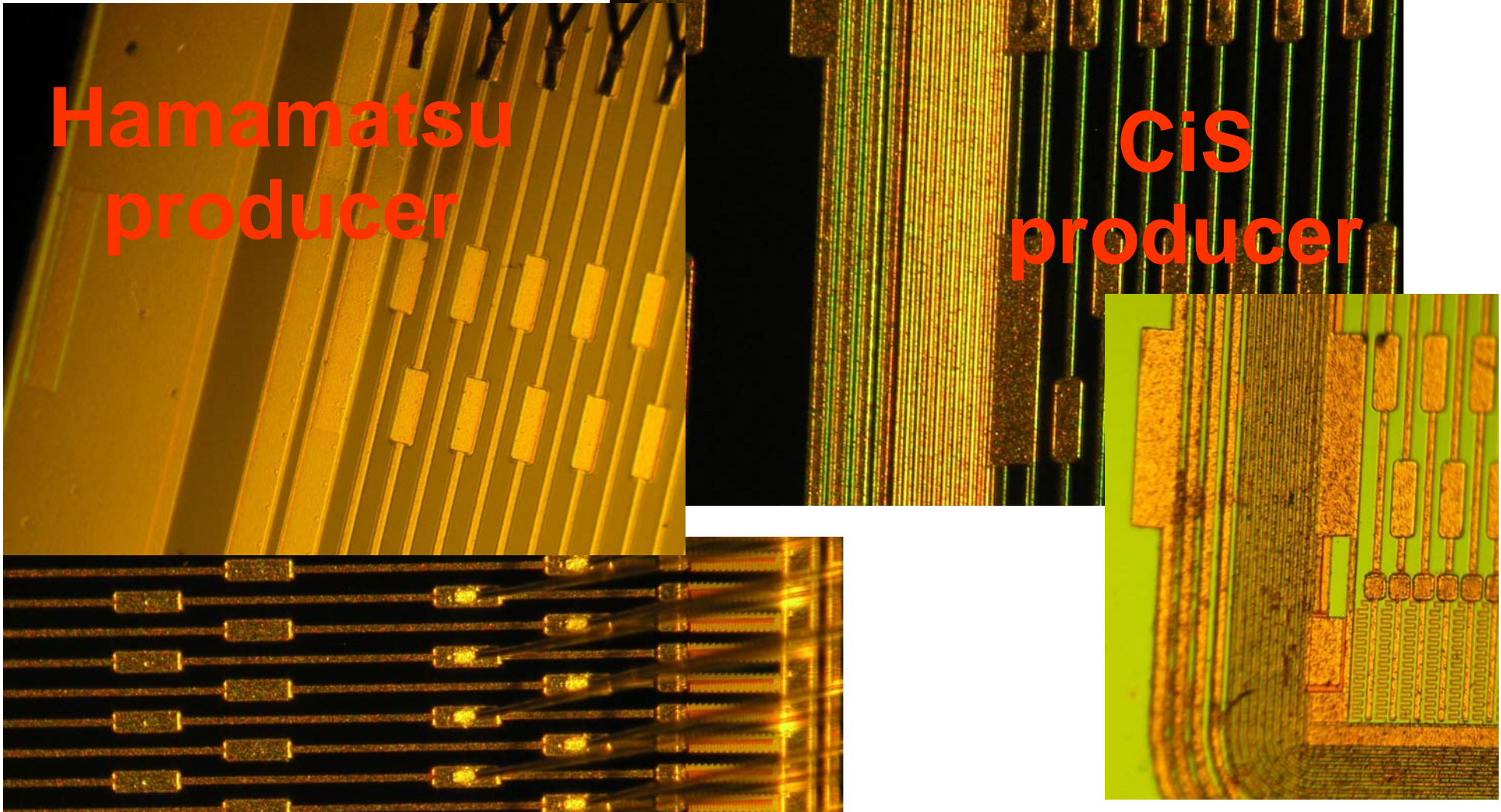
**Hamamatsu  
producer**

**CIS  
producer**





## Deeper understanding of laser beam interaction with Si detectors

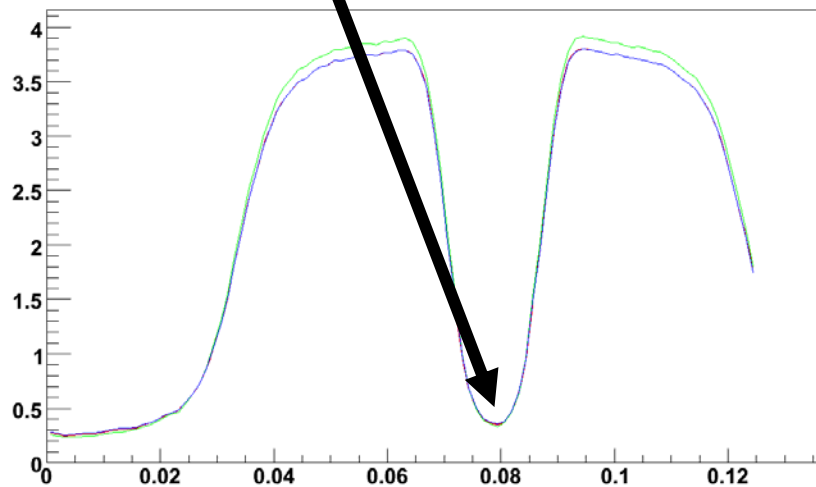




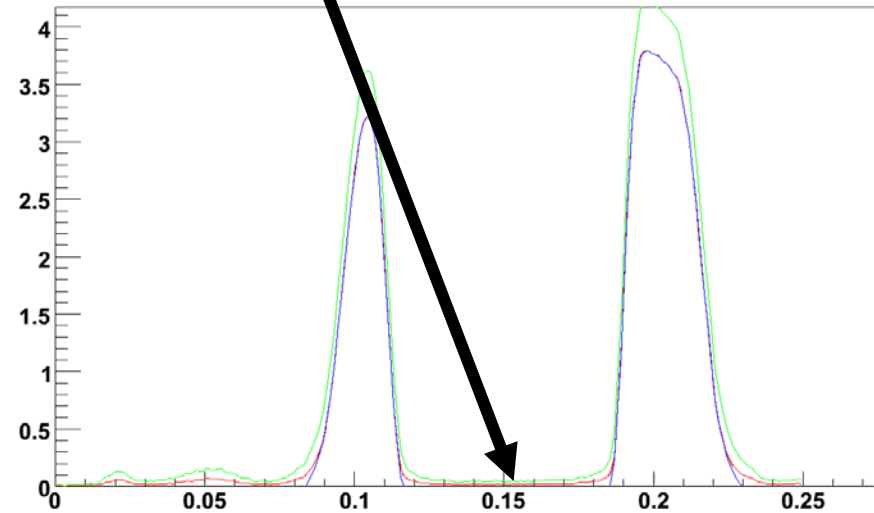
## Deeper understanding of laser beam interaction with Si detectors

# CiS producer

Response on strip with  
residuum charge sharing in  
protecting layer



Response on bond pad  
with no protection layers





## Deeper understanding of laser beam interaction with Si detectors

- Next possible effects influencing laser tests:
  - For 1060nm wavelength – thickness of silicon substrate changes: minima-maxima on interferences gives about 30% changes in charge collection in  $\frac{1}{2}$  wavelength inside Si ( $\sim 150\text{nm}$ ) – only in large area scans
  - For 650nm not fully depleted silicon in collecting time range – charge is created in layer  $< 4\mu\text{m}$  in pure electric field – depended also of properties of coating layers (electric field gradients, conductivities, lost charge vacancies,...)
  - Irradiation effects: additional diffusions, unhomogeneities



## DST data format for test beams prepared

See second talk about design of DST data format for beam tests



## Future plans/fields of interest

1. **Participation on beam tests and their analysis**
  1. Telescope preprocessing
  2. DAQ program participation
  3. DST creation in ROOT format
  4. Macros for reading and evaluation of DST
2. **Laboratory tests**
  1. Continuing on laser test of response of detector
  2. Continuing on automation of laser tests (voltage scans, position scans)
3. **Programming activities**
  1. Preparation and maintenance of standard test analysis framework for data evaluation in ROOT
4. **New fellow start on SiLC in Prague**
  1. Dr. Peter Kvasnička start in August 2006
5. **Linear collider detector simulation (both performance and microscopic)**
  1. Summer 2006 start activities on this field – PhD student Zbyněk Drásal





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## Backup slides



# Comparisons

## Tests on beam $\leftrightarrow$ beta tests $\leftrightarrow$ laser tests

- Tests on beam of high energy particles (beam tests):
  - Most similar conditions to real experiment**
  - Available only few times in year and complicated organization
  - High cost
- Tests used  $\beta$  particles from radioactive sources:
  - Lower cost and good availability, used real particles**
  - Wide spectra of energies without their measurement possibility
  - Unknown interaction point between particle and sensor, no space resolution information
- Tests with laser light:
  - Exact precise space resolution, lower cost, good availability**
  - Depth penetration setting using different light energy (wavelength)**
  - Complication on absolute efficiency measurement from energy from photon beam



# Laser tests

## Basic differences between particles and light beam in silicon:

- laser tests used beam of light with nonzero width
- different method of electron generation

## Some effects missing:

- $\delta$  – drift electrons
- energy of particles

## Some effects added:

- primary and secondary reflections



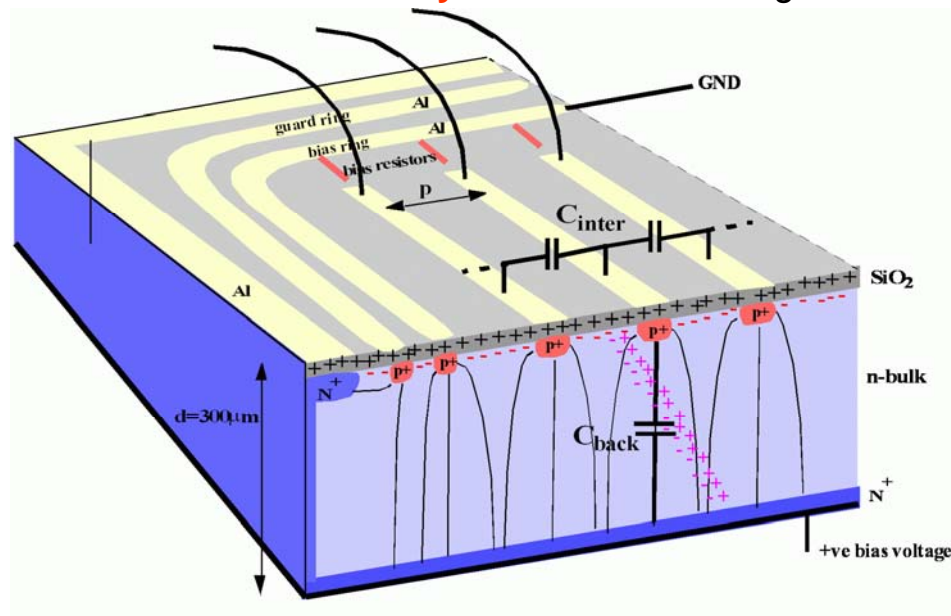
# Silicon Microstrip Detector

## Principle:

- collection of charge released in the depleted volume of a reverse biased diode
- spatial resolution through segmentation of diode
- p strips on n substrate
- AC coupling to keep leakage current away from read-out electronics
- biasing through polysilicon or implanted resistors
- Irradiation in SCT volume up to  **$1.2 \times 10^{14}$  1-MeV-n/cm<sup>2</sup> for 10 years** of LHC running

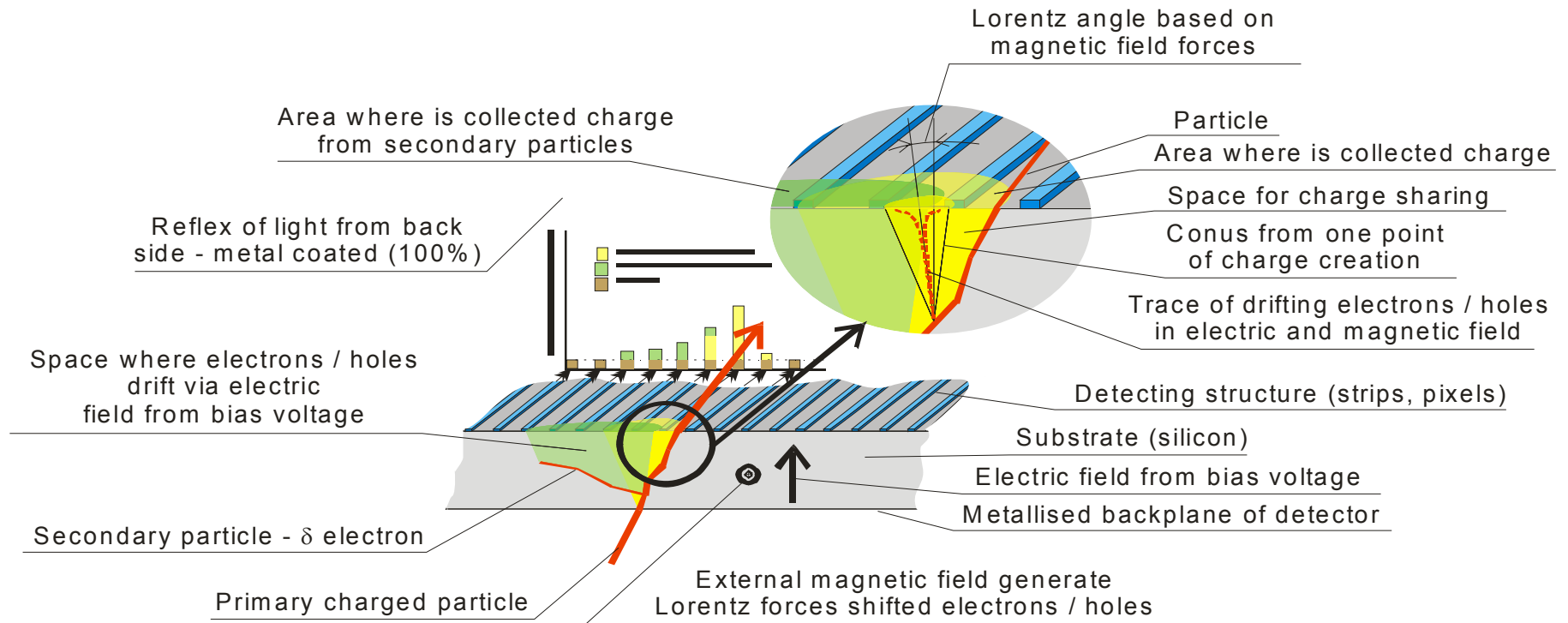
## Properties:

- leakage current
- depletion voltage and substrate resistivity
- interstrip capacitance
- backplane capacitance
- crystal orientation
- charge collection
- signal to noise



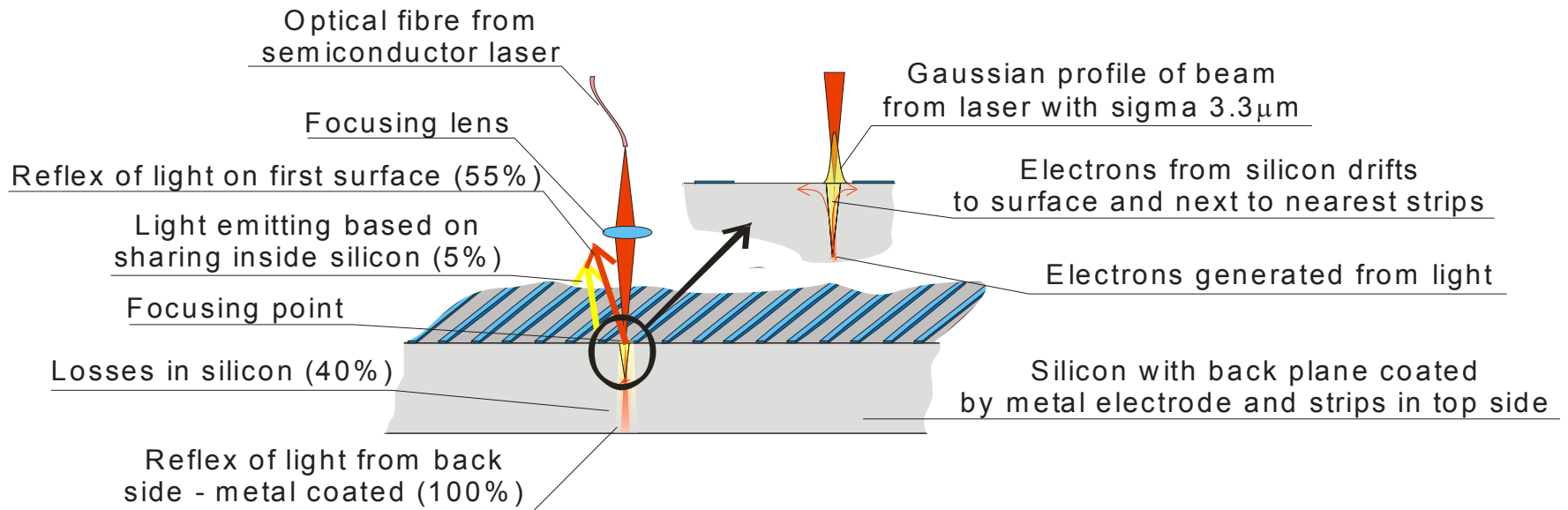


# Charge generation in silicon induced by particles



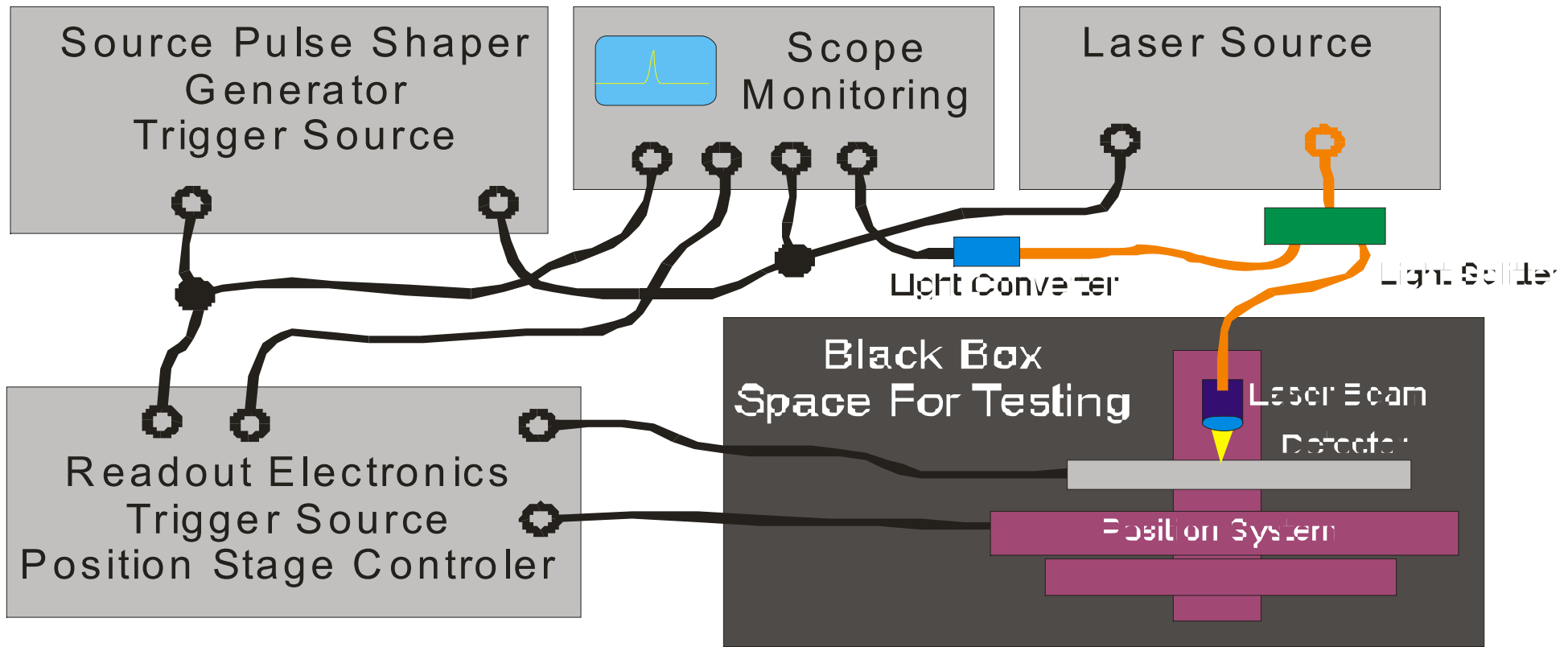


# Charge generation in silicon induced by laser beam



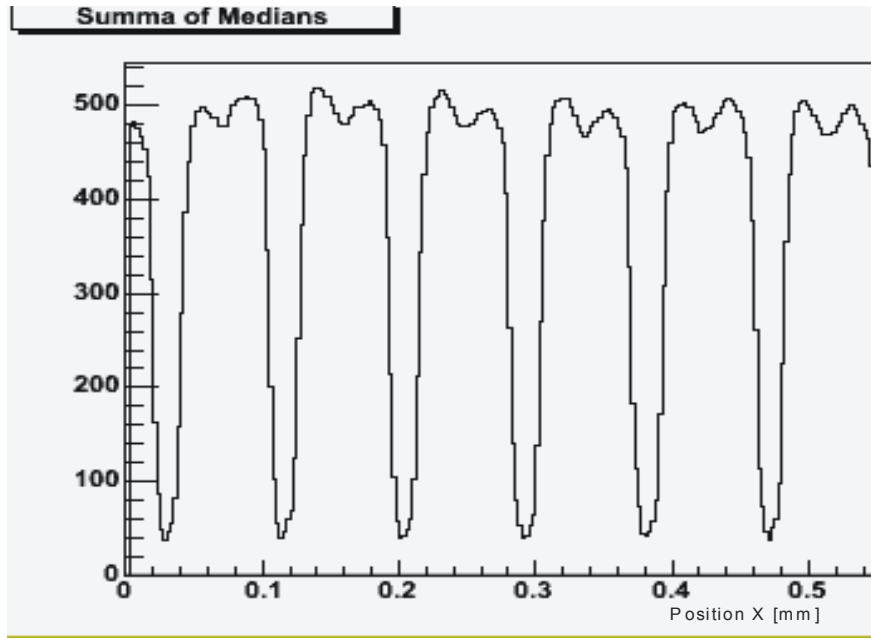


# Most typical arrangement of laser tests

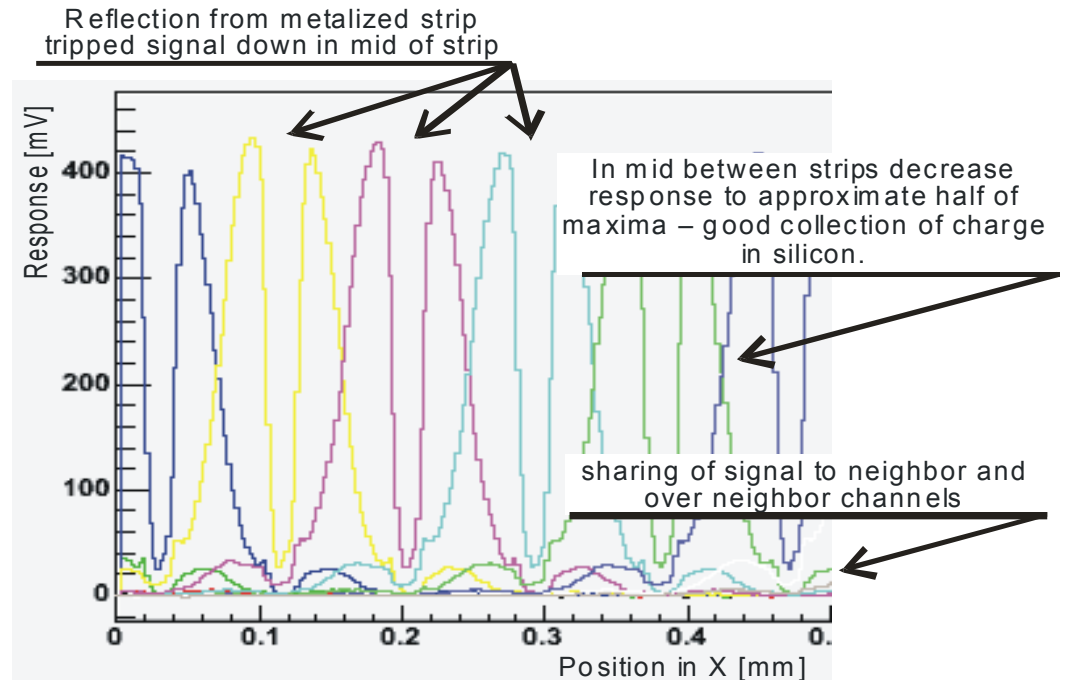




# Response of testing modules



Sum of signal of 12 adjacent strips show that collected signal in one channel is 85% from whole collected charge in detector.

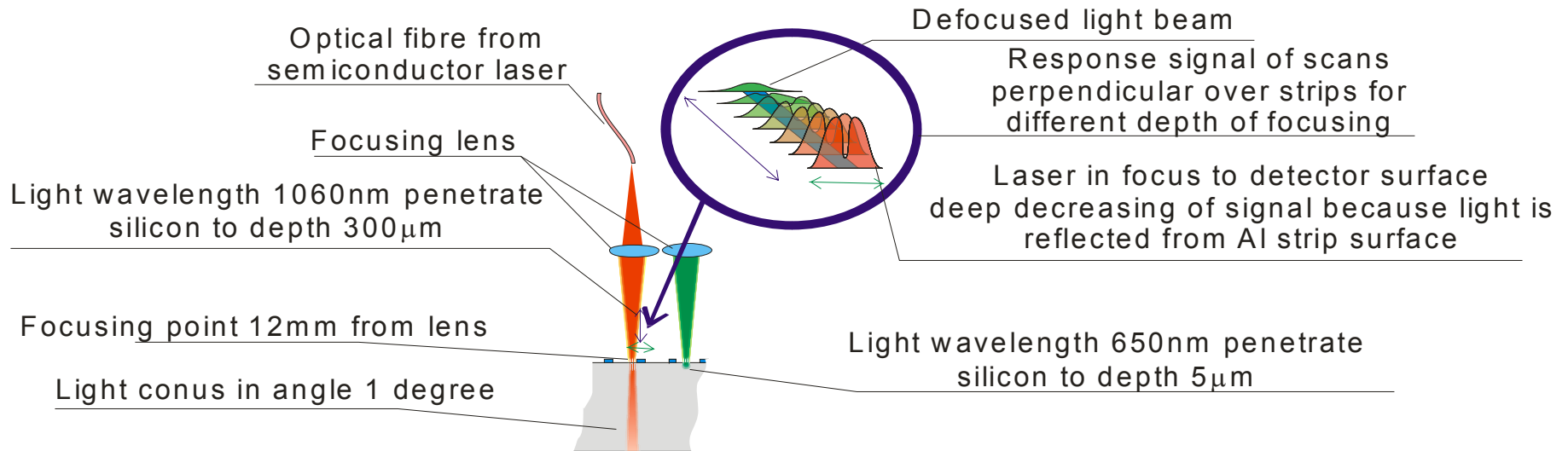


Typical response from few channels if laser beam moves across strips in best focused point.





# Laser tests - focusing



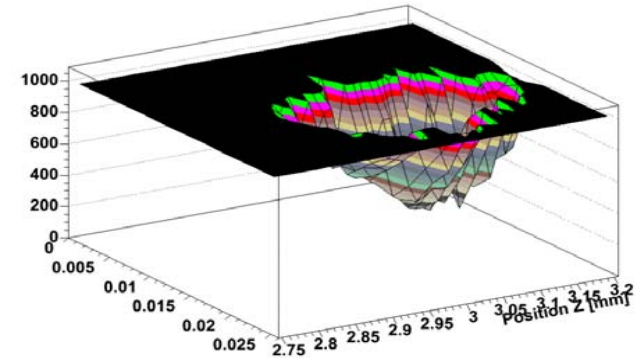
Principle used for laser focusing



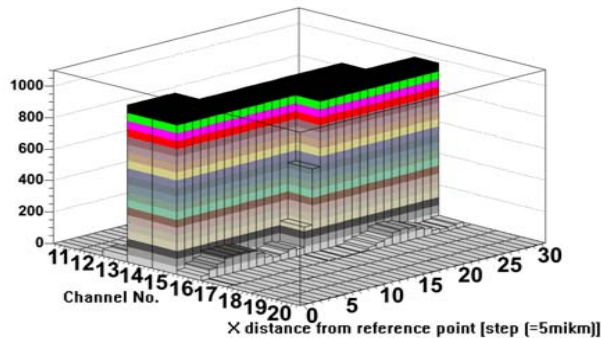
# Laser tests - focusing

*Main conclusion:* there is possibility to tune laser focusing to smallest spot using reflectivity from strip metal material, sensitivity of focusing of our type of laser output is very high, focus range is less 50  $\mu\text{m}$  (from factory is declared good focus range about 1 mm).

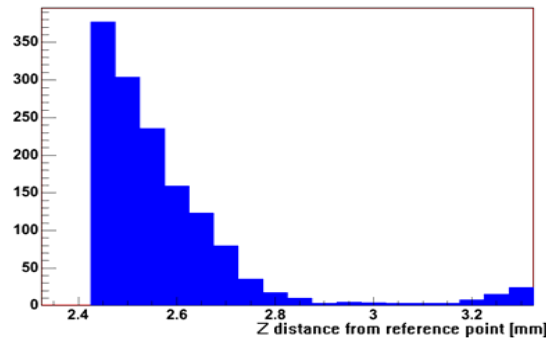
Tuning of laser spot in Z - Main



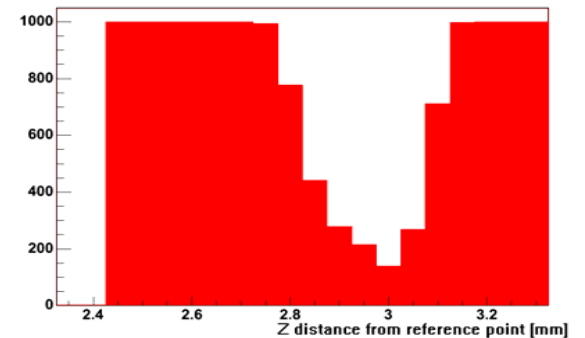
Laser Scan - ALL VALUE



Tuning of laser spot in Z - minimum neighbors



Tuning of laser spot in Z - minimum main





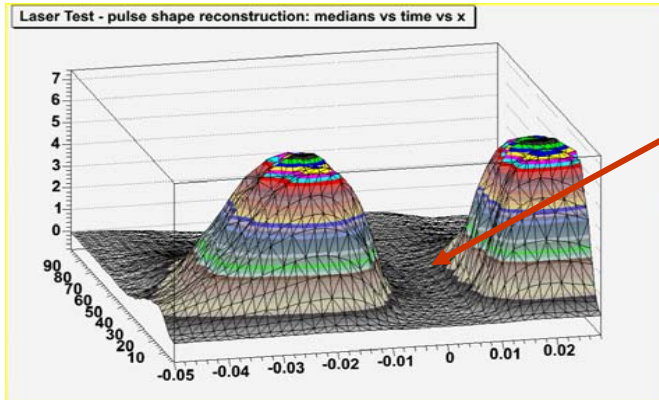
# Laser Tests - Applications

Numerous tests of ATLAS end cap SCT modules were developed and performed:

- The **bond mixing test** done up to 30 minutes per detector – test for production modules
- The **channels from mask file (bad channels)** tested independently using two methods
- **Punch through (pin hole) channels** test (gain confirmation) for response
- **Pulse shape reconstruction**
- Test of **homogeneity of response** from detector in full area is possible
- Detail **response vs. inter-strip** position
- **Bias scan** of detectors
- **Temperature scan**
- Spatial resolution of **noise bump-strips on CiS detectors** was checked and measured



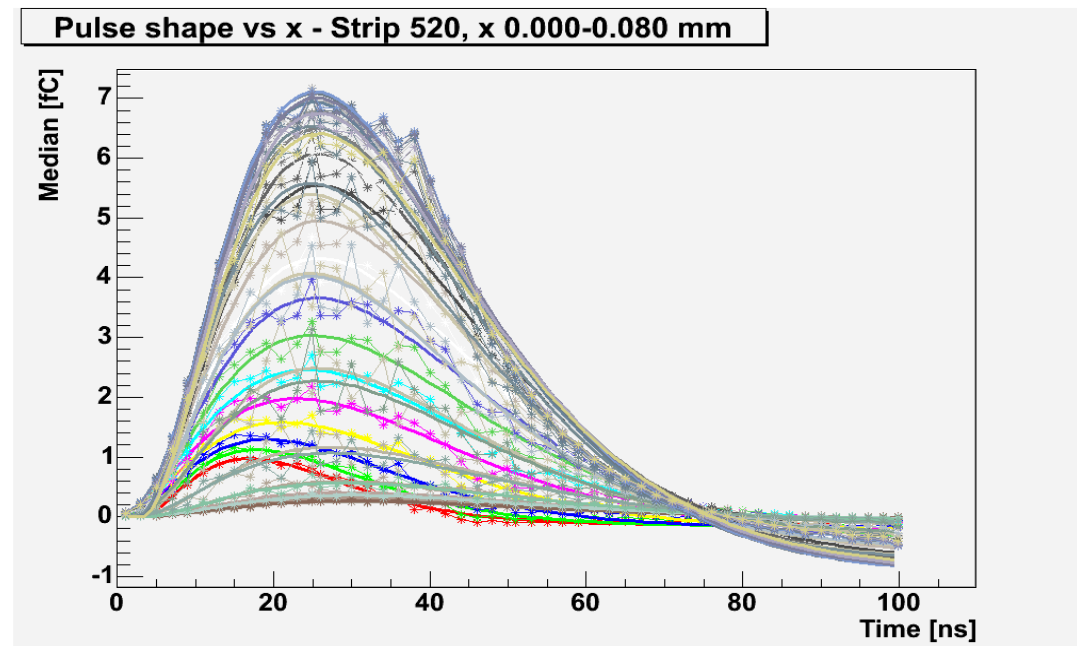
# Pulse shape reconstruction



Strip  
position

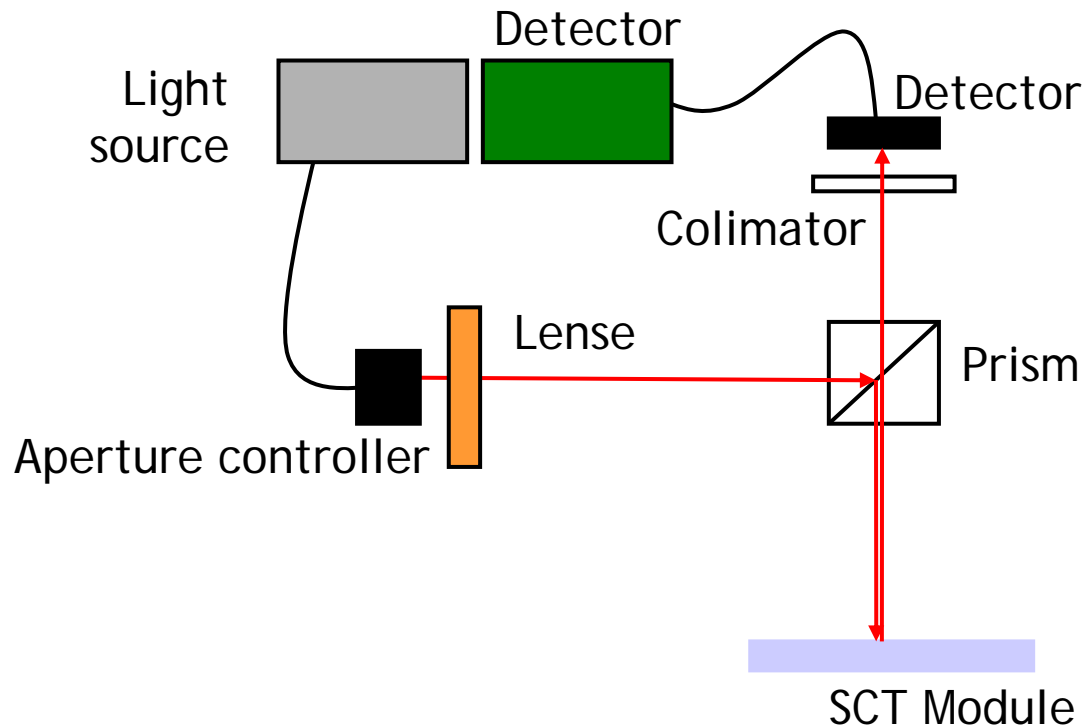
2D graph of medians in time shift vs.  $x$ , strip metal part is on point 0 where practically whole light beam is reflected out

*Pulse shape fit for all  $x$  positions*



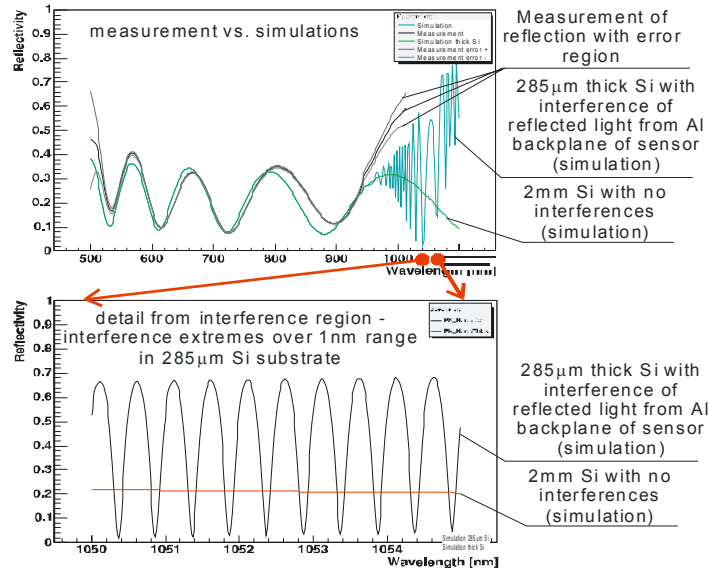


# Reflectivity measurement

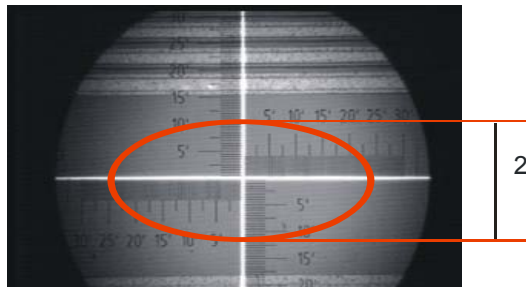




# Optical properties



Plots comparing reflectivity measurement and calculation from thickness of layers in range 300 - 1100nm of wavelength



200  $\mu\text{m}$

- Absolute response measurements are problematic:**
- deposition of defined charge in the sensor is difficult because of many optical effects:**
- part of light is **reflected**
  - sometime transparent layers are **not homogenous** because technology of covering use also transport of atoms between layers so borders between layers are gradients and no steps
  - refractive index for some materials must be measured because **big spread of value** depends of using deposition and surface polishing technology
  - thick and **transparent substrates** gives hardly defined conditions for reflectivity calculation
  - **the best is use the same laser beam for also reflectivity measurement** (method of this is on the way)

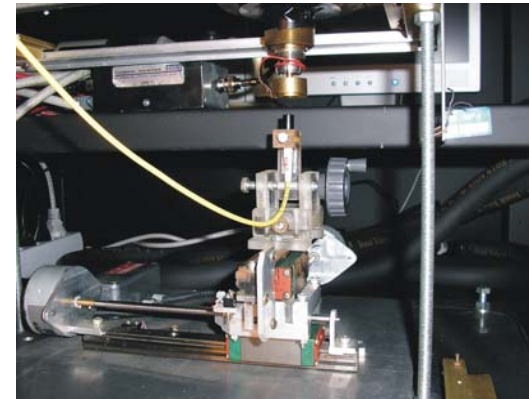
**Refractive index and thickness of layers was measured on spot in range 300 - 800nm of wavelength.**



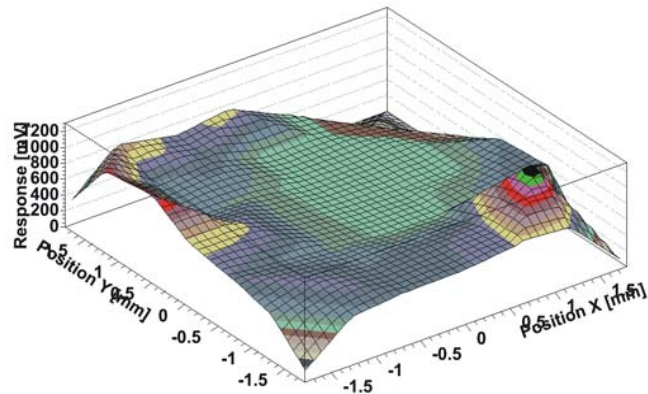
# New Tests

- large area diodes tests
- depfet structures

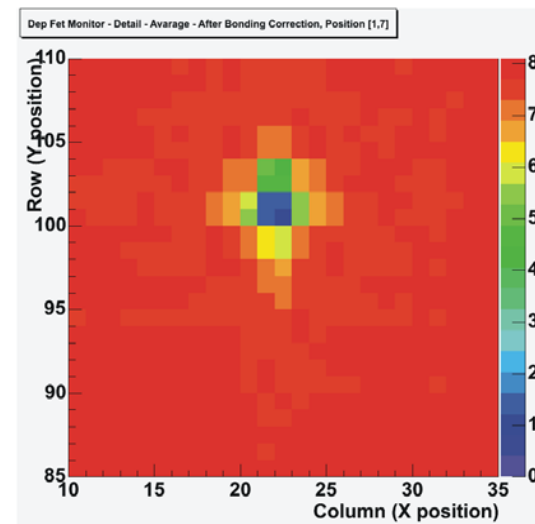
Stability of laser pulse:  
 Amplitude:  $\sigma < 1.5\%$  @ 1.8MeV deposited  
 Timing jitter:  $\sigma < 0.4\text{ns}$  @ 32MeV deposited



Arrangement of tests



Response of Si pad detector for  
1060nm light wavelength



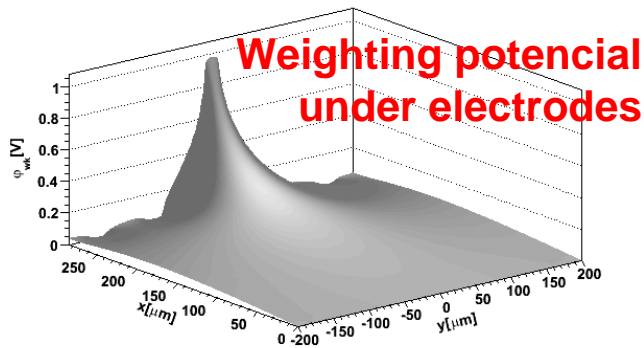
Response of DEPDET detector



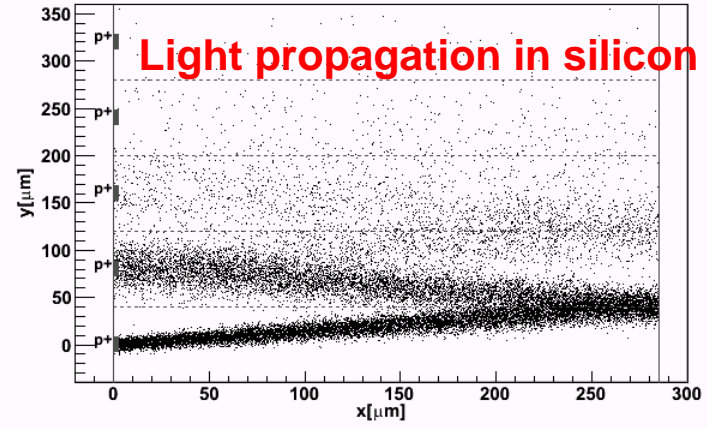
# Laser Tests And Simulations

How is signal on detector created

Weighting potential associated to the  $k^{\text{th}}$  electrode



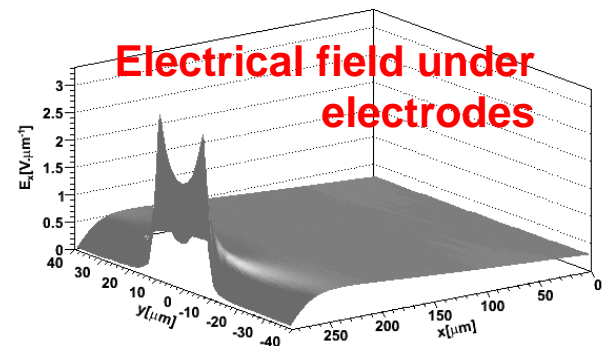
2D distr. of generated e-h pairs  $\approx 4fC$ ,  $\alpha_{in} = 30^\circ$ ,  $div = 0.5^\circ$



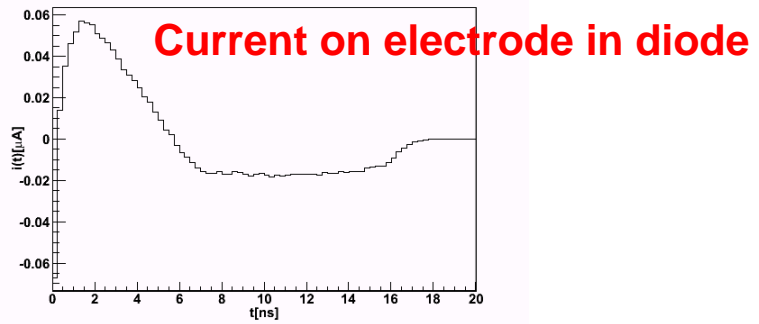
Cooperation:

- University of Bari (Italy)
- Lappeenranta University of Technology (Finland)

$E_x$  in an elementary cell



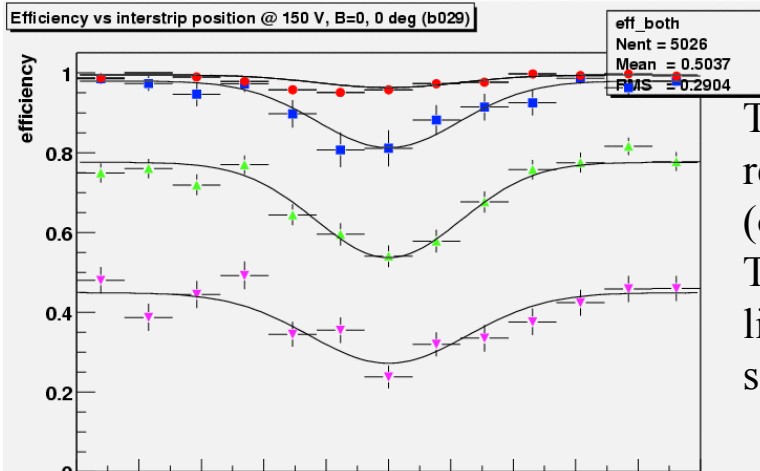
Current pulse - strip on the lefside from central strip



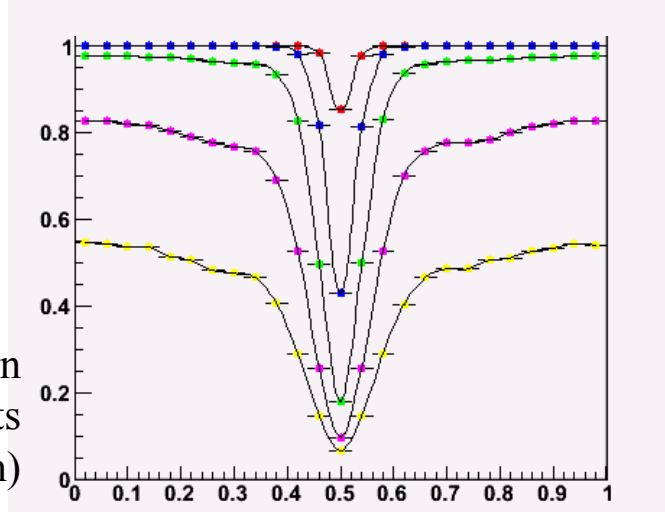
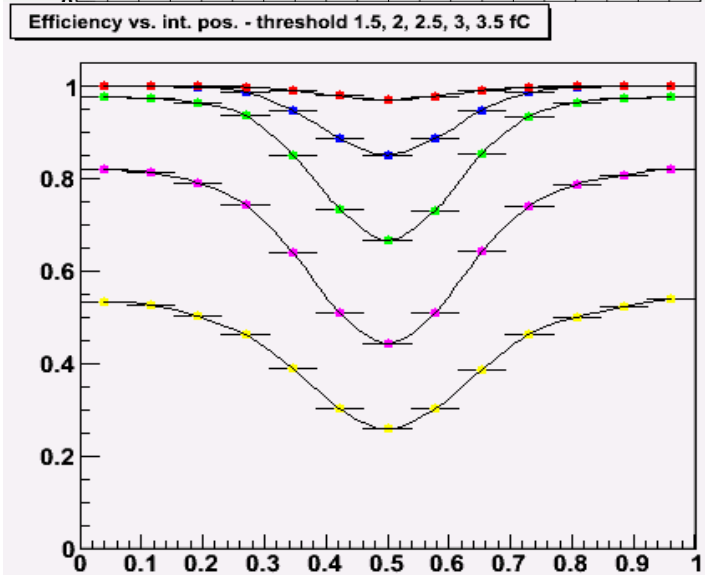
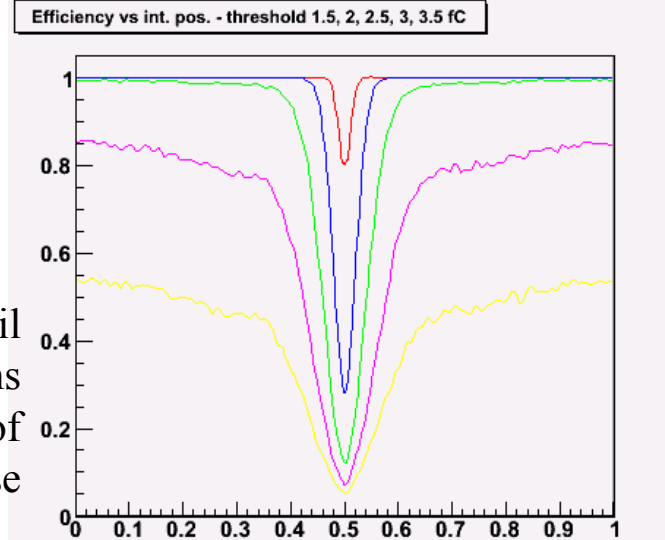




# Space Resolutions Measurements



Test beam  
results  
( $\sigma \approx 10 \mu\text{m}$ )  
Telescope  
limitation &  
scattering





# Cooperation

- Help in building of new laser test laboratories: MPI Mnichov, University Freiburg
- Looking for examples for testing around
- Cooperation with:
  - ÚŘE AVČR Prague
  - University of Freiburg
  - MPI Mnichov
  - University of Bonn
  - University of Lancaster
  - University of Bari
  - Lappeenranta University of Technology



# Conclusions

## Laser tests are useful in:

- precise space resolution studies
- time walk and time shape measurements
- functionality of problematic part of detectors
- surface charge collection and deep charge generation from 4 mm@650nm up to 1mm@1060nm

## Quality of tests depends from:

- top layers: thickness, refractive index, surface quality
- geometry of pads on top, their material, surface of them, protected layers
- laser light beam quality, coherent properties, long time stability, aperture, wavelength



# Usability

## Laser test are:

- extremely useful for **tuning of individual sensor and readout settings to find optimal working parameters**
- good for **comparison between the same type of detectors** with exactly the same top surface properties
- of **limited use in absolute measurement of efficiency** of semiconductor detectors (under study)

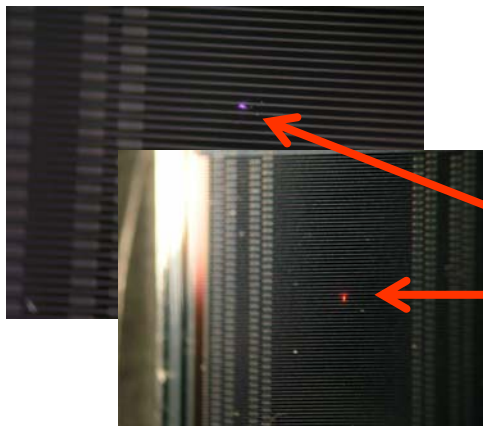


# Place Of Laser Tests



Clean room  
in Prague  
Charles  
University  
with laser  
black box  
and readout  
electronics  
stands

Visual inspection place



Laser spot  
on detectors  
in 1060nm  
and 660 nm  
wavelength,  
strip pitch is  
80  $\mu\text{m}$

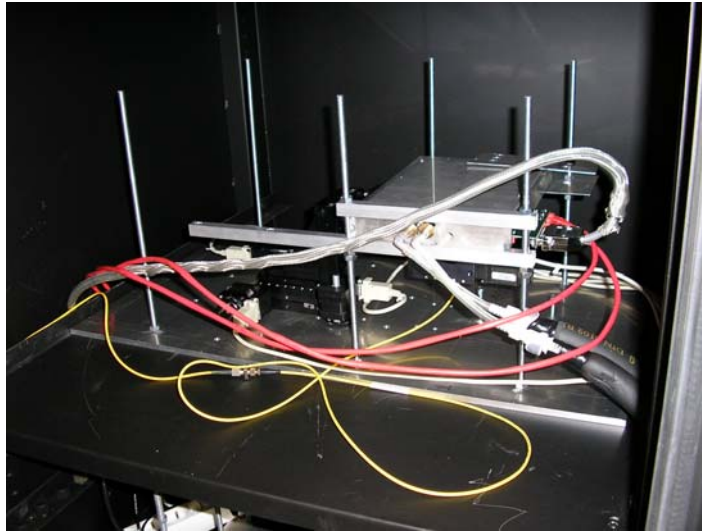


Black box for  
laser test  
measurements

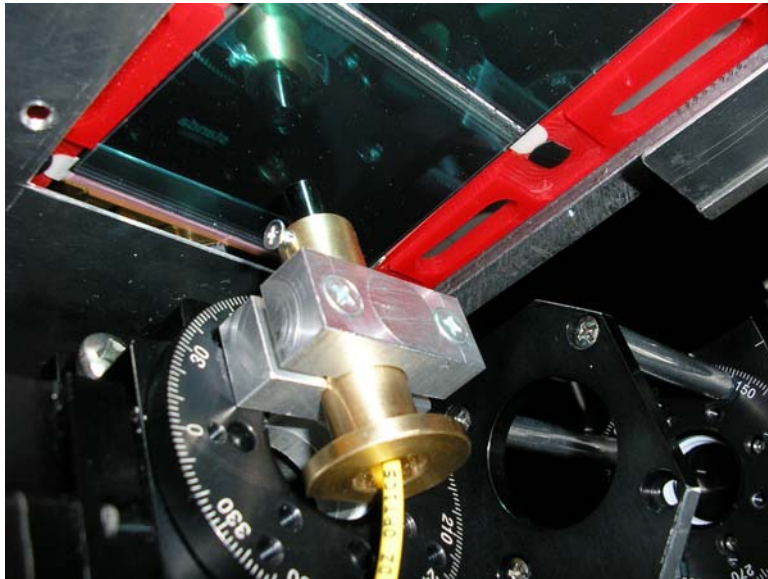
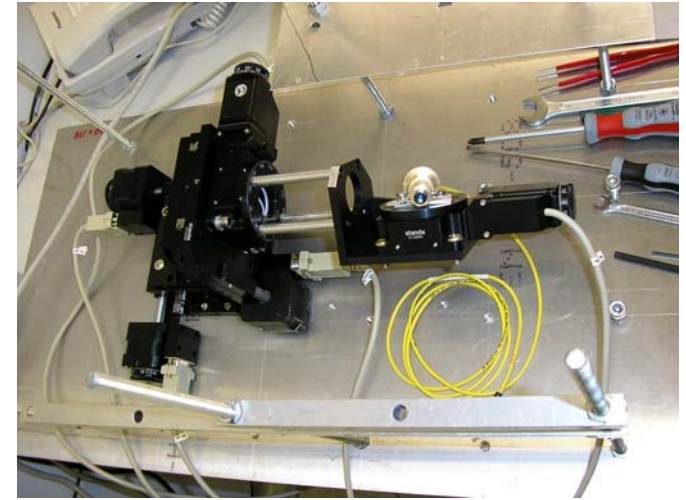


Charles University  
Prague

Arrange  
ment in  
black  
box



3D2R Laser System



Lighting to detector

3D2R  
moving  
system

Tilting of laser  
beam before  
mounting of  
detector

